

TOSHIBA PHOTO IC SILICON EPITAXIAL PLANAR

TPS808

PHOTO IC FOR PHOTO INTERRUPTER

Unit in mm

PHOTOELECTRIC COUNTER

POSITION AND ROTATIONAL SPEED SENSOR

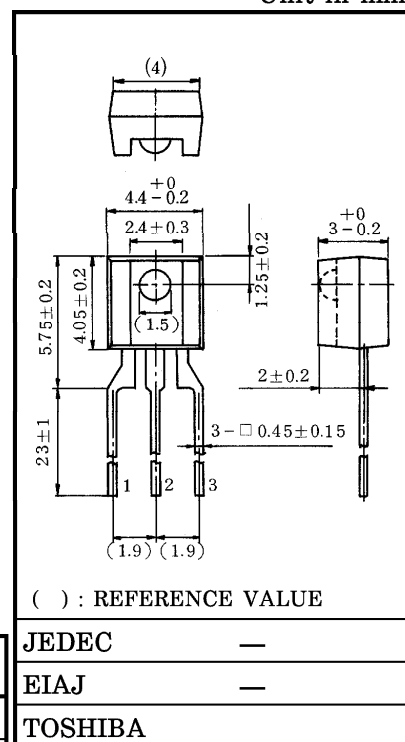
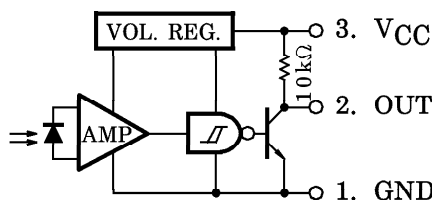
- TPS808 is a photo IC integrating photo diode, amplifier circuit and waveform shaping circuit in 1 chip.
- Visible light cut resin is used. : $\lambda_P=900\text{nm}$ (TYP.)
- The same external shape as the infrared LED TLN107A, and is best suited for combination with TLN107A as a photo interrupter.
- High speed response : $t_{pLH}=6\mu\text{s}$, $t_{pHL}=2\mu\text{s}$ (TYP.)
- When light is received, output becomes low level.

MAXIMUM RATINGS (T_a = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	17	V
High Level Output Voltage	V _{OH}	V _{CC} (Note)	V
Low Level Output Voltage	I _{OL}	50	mA
Low Level Output Current Derating (Ta > 25°C)	ΔI _{OL} / °C	−0.67	mA / °C
Power Dissipation	P _O	250	mW
Power Dissipation Derating (Ta > 25°C)	ΔP _O / °C	−3.33	mW / °C
Operating Temperature Range	T _{opr}	−25~85	°C
Storage Temperature Range	T _{stg}	−40~100	°C
Soldering Temperature (5s)	T _{sol}	260	°C

Note : V_{OH} keeps under V_{CC} Voltage.

PIN CONNECTION



Weight : 0.19g (TYP.)

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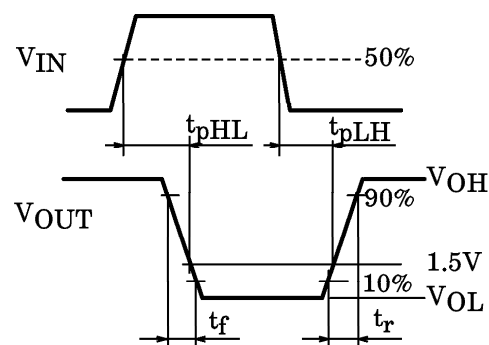
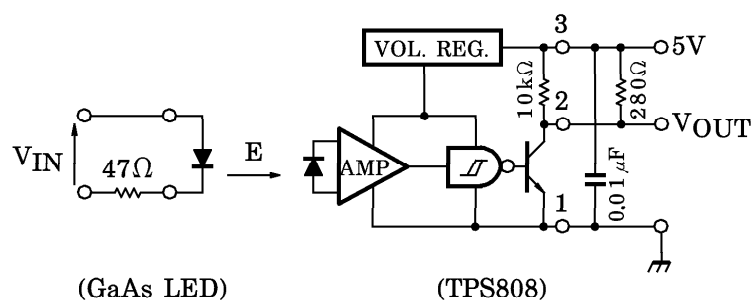
OPTO-ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

($T_a = 0 \sim 70^\circ\text{C}$, Characteristics with no entry of $T_a = 25^\circ\text{C}$ in the test conditions. Typical values are all at 25°C .)

CHARACTERISTIC			SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage			V _{CC}	—	4.5	—	17	V
Low Level Output Voltage			V _{OL}	I _{OL} =16mA, V _{CC} =5V E=2mW / cm ²	—	0.07	0.4	V
High Level Output Voltage			V _{OH}	V _{CC} =5V, E=0	4.5	5	—	V
Supply Current	Low Level	I _{CCL}	V _{CC} =5V, E=2mW / cm ²		—	3.0	5.5	mA
	High Level	I _{CCH}	V _{CC} =5V, E=0		—	1.2	3	mA
“H”→“L” Threshold Radiant Incidence (Note 1)		E _{HL}	V _{CC} =5V, Ta=25°C		—	0.1	0.3	mW / cm ²
			V _{CC} =5V		—	—	0.6	
Histerisis Ratio		E _{LH} / E _{HL}	Ta=25°C, V _{CC} =5V		—	0.65	—	—
Peak Sensitivity Wavelength		λ _P	—		—	900	—	nm
Switching Time	Propagation Delay Time	“L”→“H”	t _{pLH}	Ta=25°C, V _{CC} =5V E=2mW / cm ² R _L =280Ω (Note 2)	—	6	—	μs
		“H”→“L”	t _{pHL}		—	2	—	
	Rise Time		t _r		—	0.1	—	
	Fall Time		t _f		—	0.03	—	

Note 1 : Color temperature = 2870°K , Standard Tungsten Lamp.

Note 2 : Switching time test circuit.



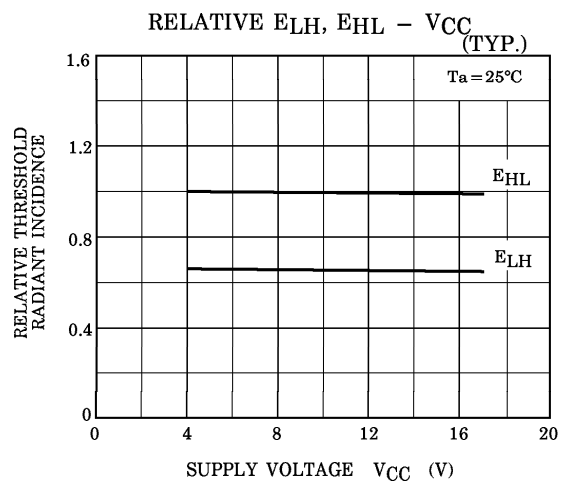
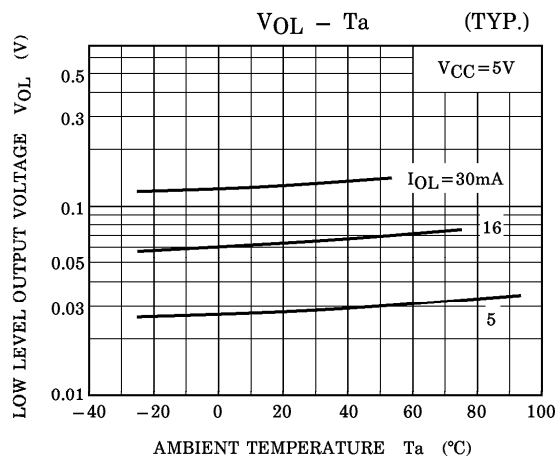
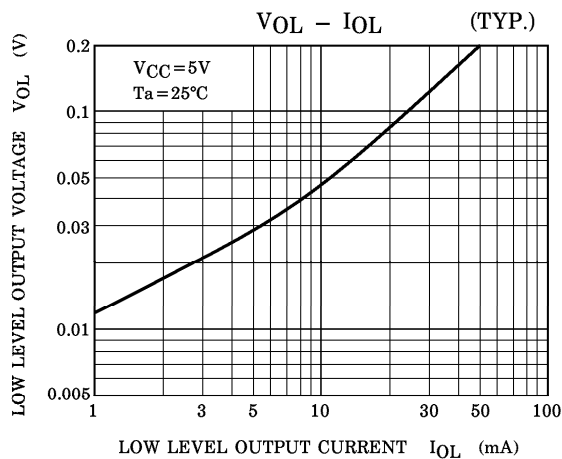
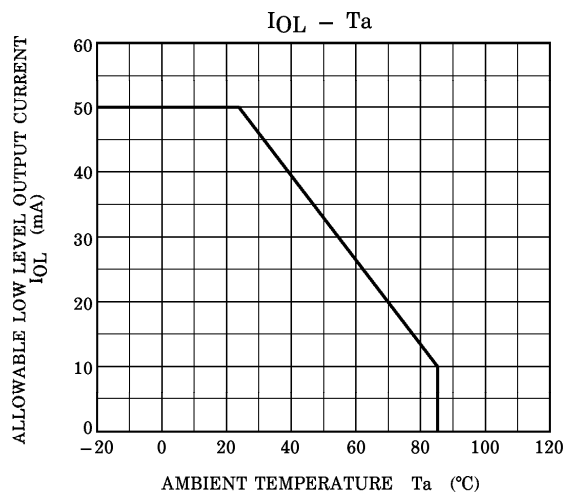
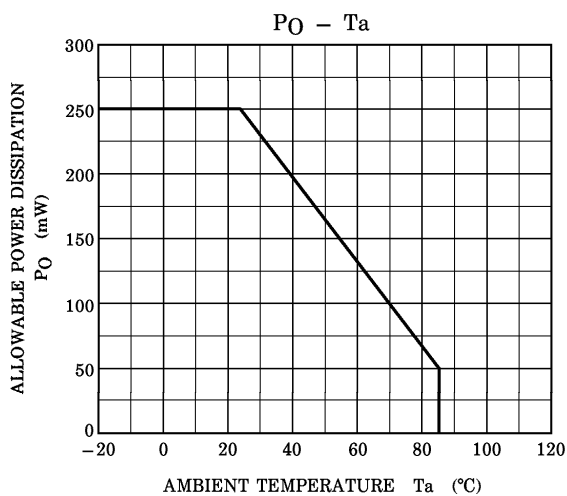
RECOMMENDED OPERATING CONDITIONS

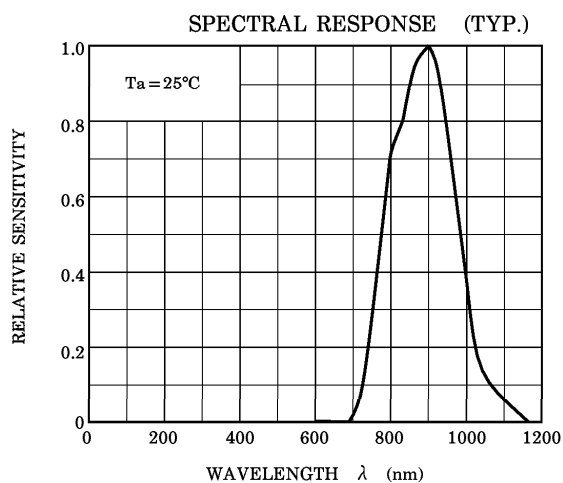
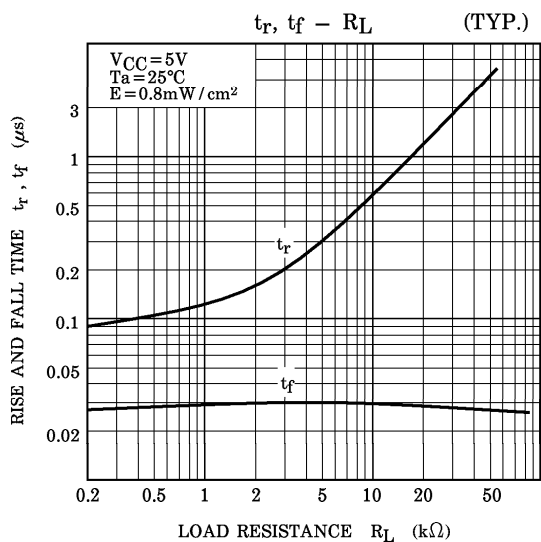
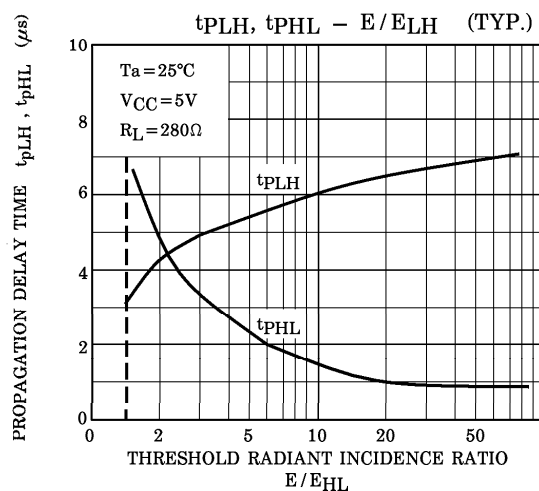
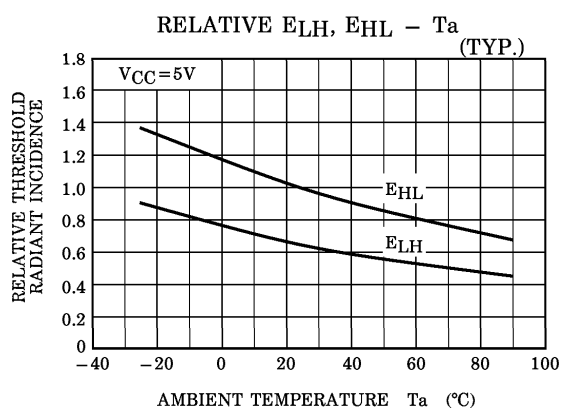
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	4.5	5	16	V
High Level Output Voltage	V _{OH}	4.5	—	V _{CC}	V
Radiant Incidence	E	0.8	—	—	mW / cm ²
Operating Temperature	T _{opr}	0	—	70	°C

PRECAUTION

Please be careful of the followings.

1. If the lead is formed, the lead should be formed at a distance of 2mm from the body of the device.
Soldering shall be performed after lead forming.
(Soldering portion of lead : above 2mm from the body of the device)
2. Supply the by-pass condenser up to 0.01 μ F between V_{CC} and GND near device to stabilize the power supply line.
3. During 100 μ s after turning on V_{CC}, output voltage changes for stabilizing the inner circuit.





DIRECTIONAL SENSITIVITY CHARACTERISTIC (TYP.)
($T_a=25^\circ C$)

